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A Fault Tolerant PMAD System Using Radiation Hardened Highly Integrated AFE Circuits

Sorin A. Spanoche and Mathieu Sureau

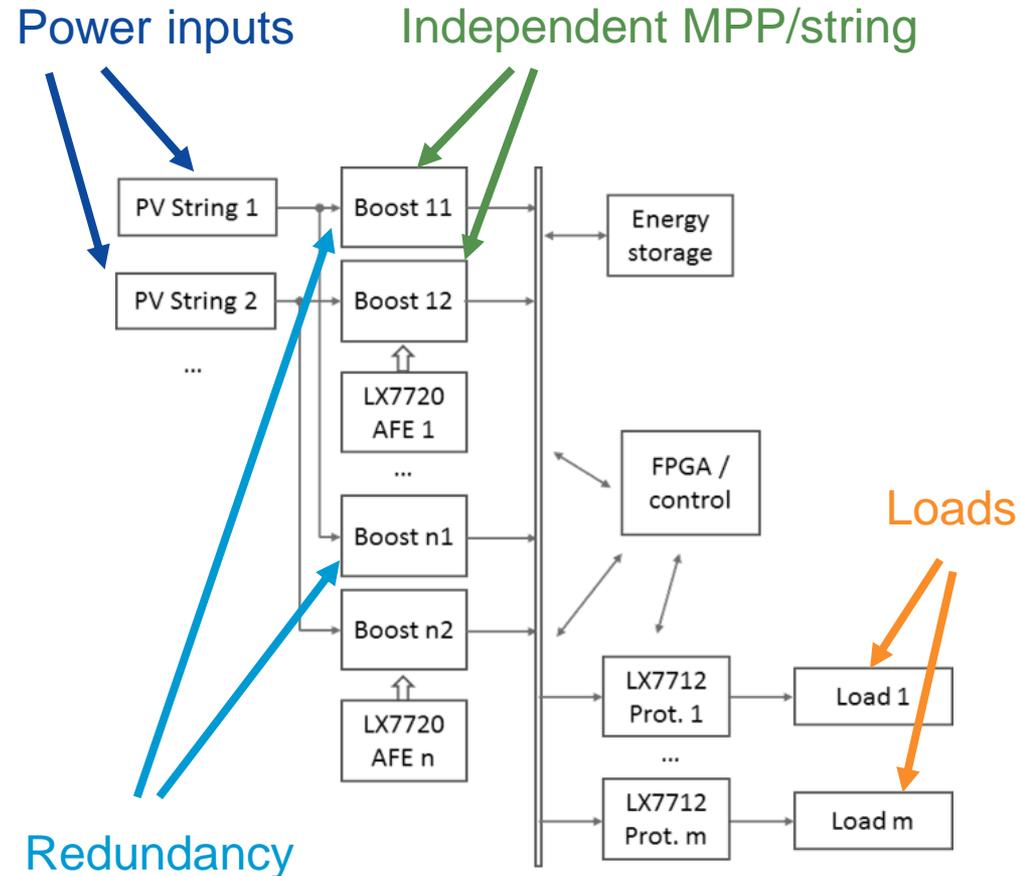
Agenda

- PMAD topology
- Fault Tolerant Power Stage
- LX7720 as analog front-end for DC/DC conversion
- LX7712 as power line protection for PMAD
- Control aspects

PMAD Topology

Power Management and Distribution

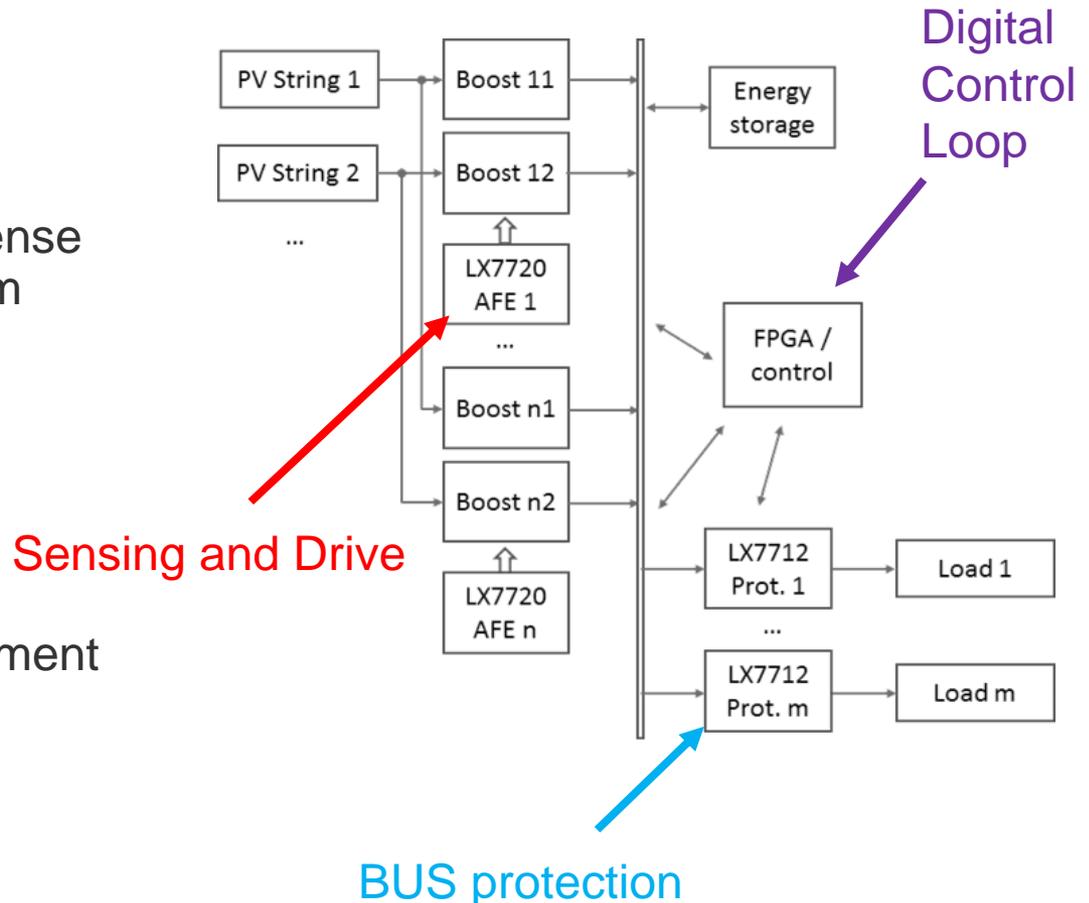
- Optimally transfers power from input sources, manages transmission of power to loads
- Consists of DC/DC converters, protection circuits, power transfer and fault management
- Inputs assumed as PV strings with fast MPPT control to track
 - Varying angle
 - Shading
 - Temperature per spring



PMAD Topology

Sensing, Drive and Control

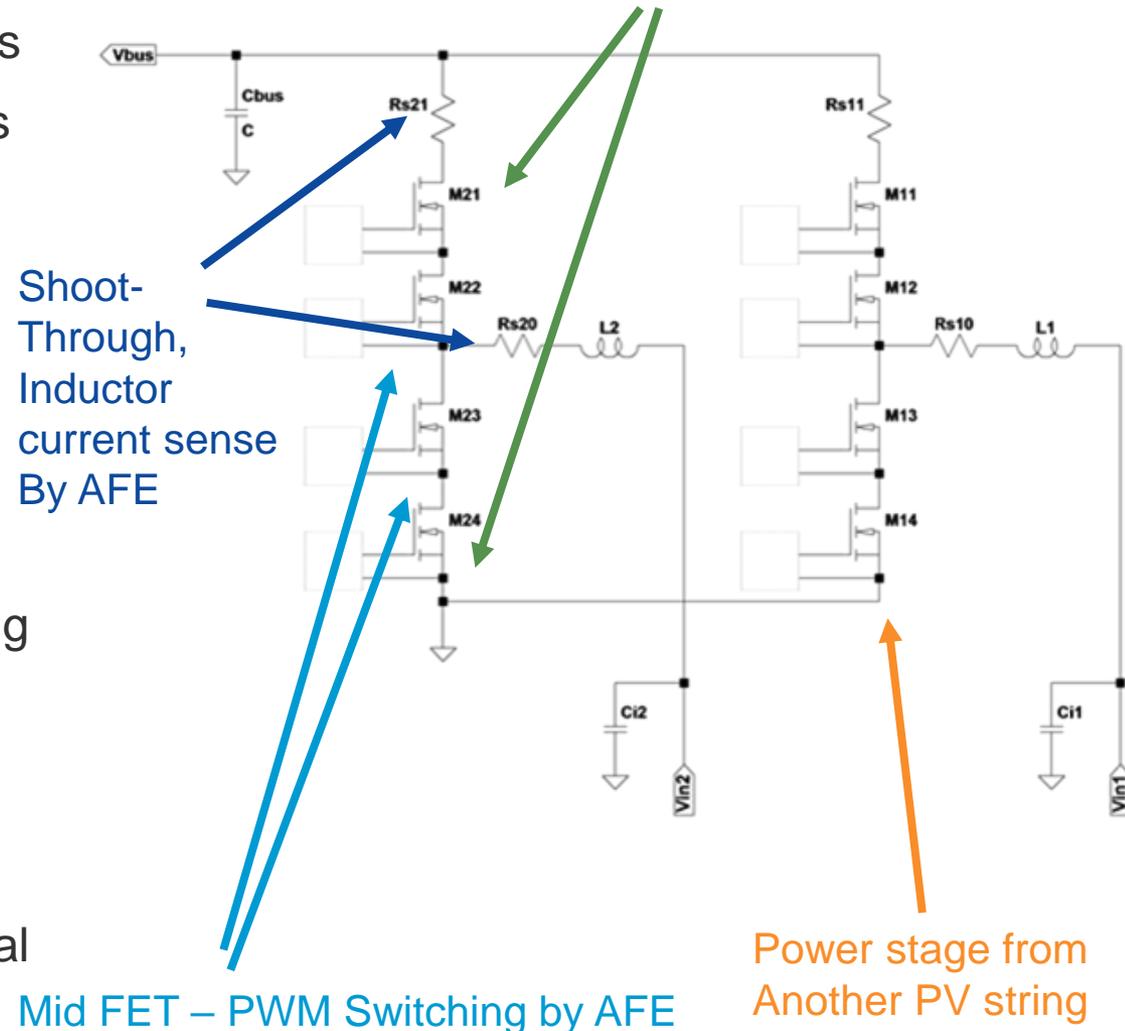
- Voltages on input and output nodes and currents in each converter are sensed
- Loop control if done digitally
 - AFE converts to digital all sense lines + drives MOSFETs from PWM inputs
 - FPGA implements
 - DC/DC loop
 - MPPT
 - Power and safety management
- Power Distribution and Bus Protection implemented



Power stage

- DC/DC units implemented using
 - 2 High-Side NMOS in series
 - 2 Low-Side NMOS in series
 - + Allows for FET short protection
 - - Efficiency penalty
- Regular switching Mid FETs – M22 M23
- Health Monitoring by exercising upper and Lower FETs – M21 and M24
- Shoot through current or inductor current detect to signal Fault

Upper – Lower FETs Health Monitor



Power stage fault simulation

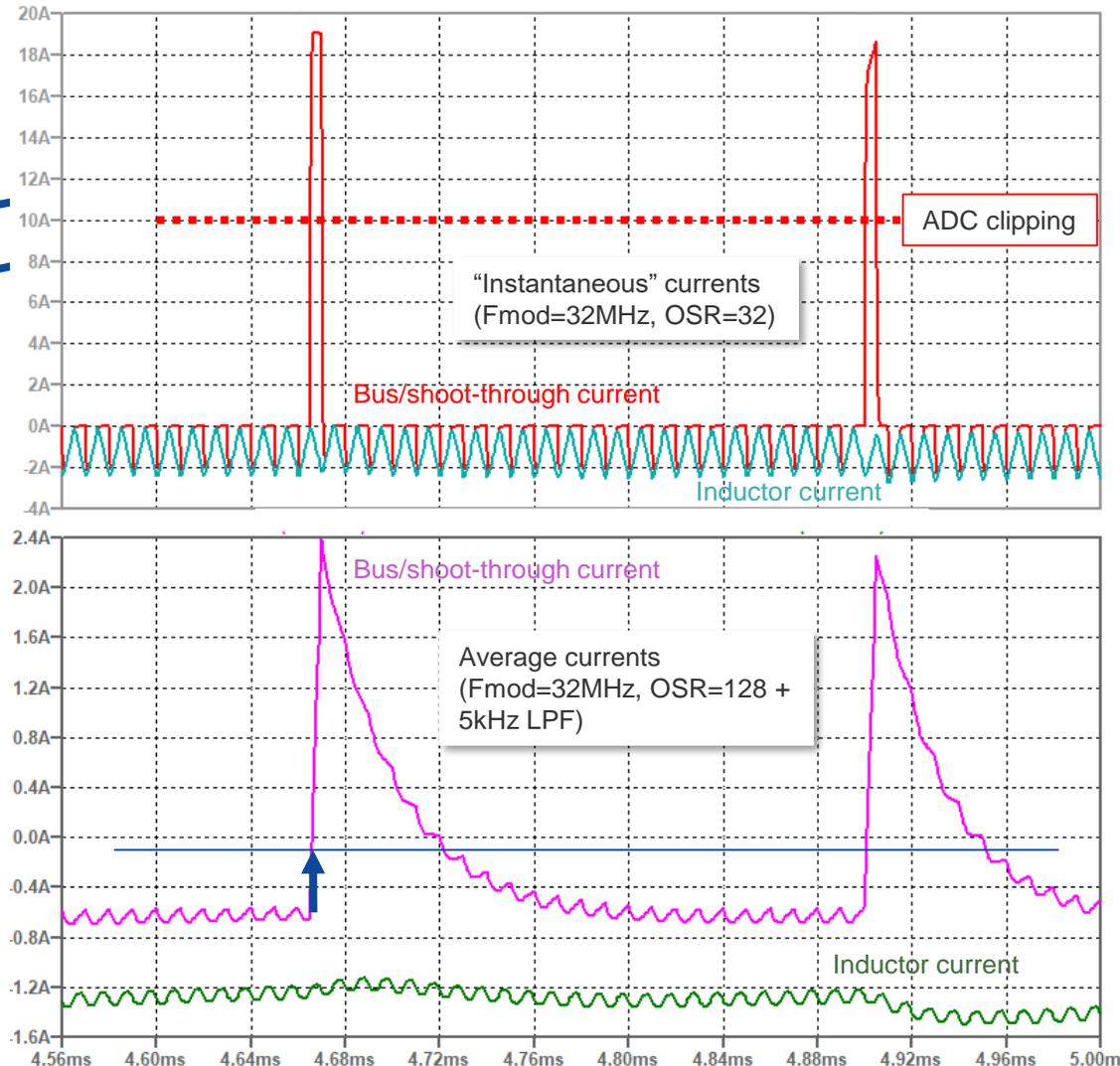
- Fault detect waveforms with 5 Ohms faults

- on M14/M24
- on M11/M21

- Criteria in this case:

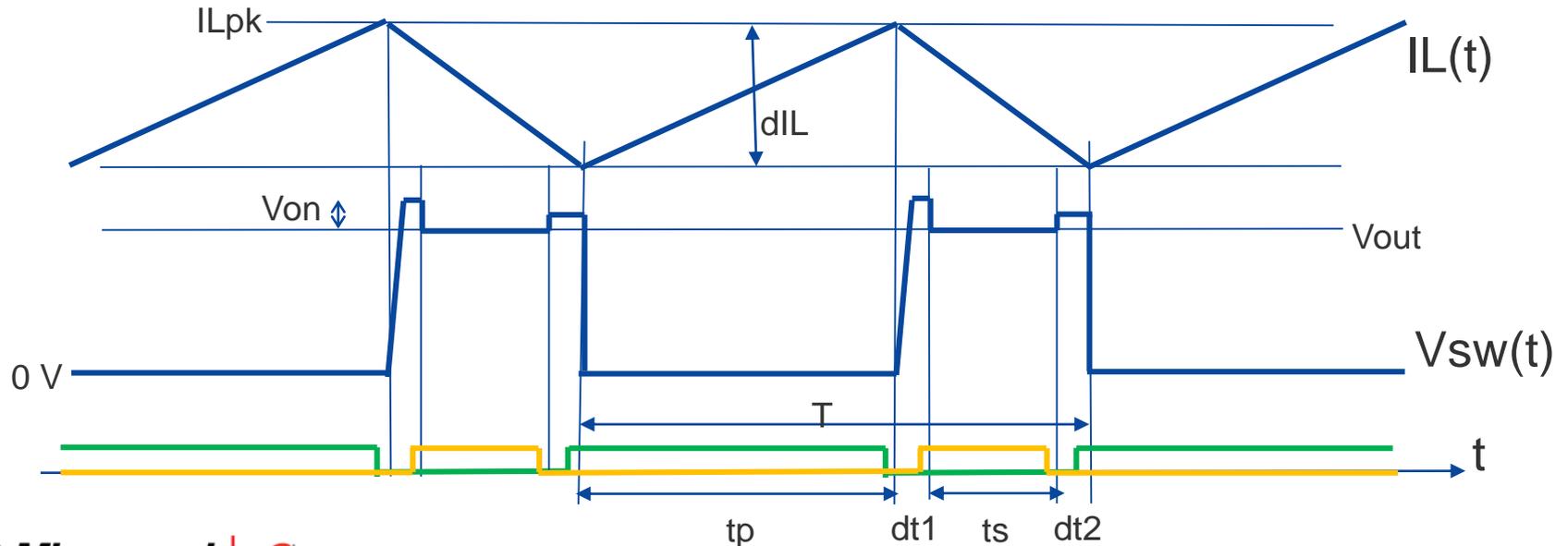
“If the change in average current during the test switching cycle is higher than 0.5A then tested device is developing a short.”

Note: Inductor current is almost unaffected (same for output and input voltages)



Dead time simple model

- For Synchronous Boost in CCM: if $dt1$ and $dt2$ are too large they impact efficiency so $dt1,2$ should be minimized.
- If $dt1$ and $dt2$ are negative then a large shoot through current will reduce efficiency
- There is a maximum efficiency point



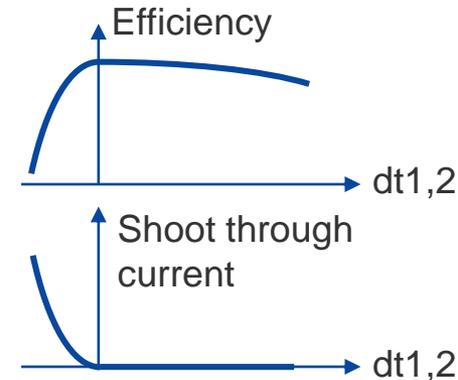
Dead time simple model cont.

- For $dt > 0$ degradation is sub percent for 100V output.
- Efficiency degrades most when dt is negative (there is shoot through current).

$$\eta \approx 1 - \frac{V_{out}^2 / R_{short} |dt|}{V_{out}^2 / R_{load} T} = 1 - \frac{|dt|}{T} \times \frac{R_{load}}{R_{short}}$$

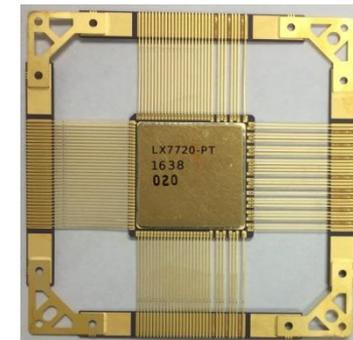
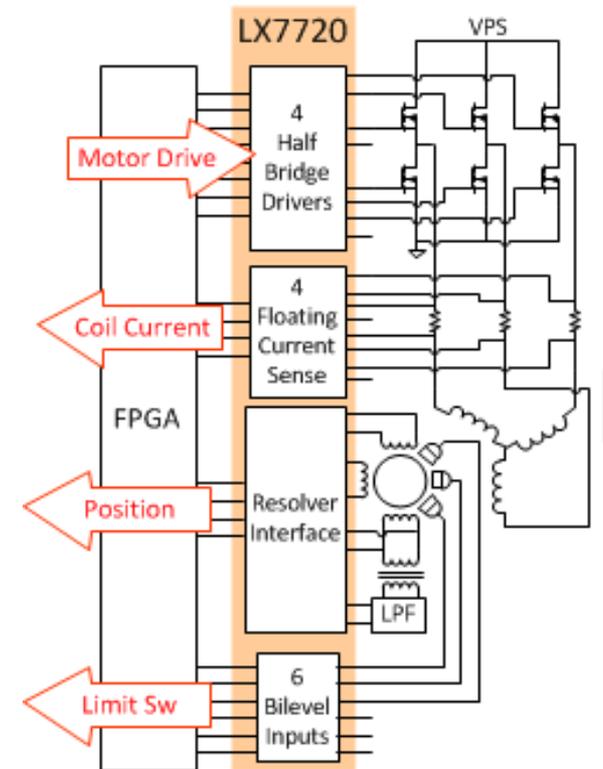
For example for $dt = -1\text{ns}$, $T = 10\mu\text{s}$, $R_{load} = 300\Omega$, $R_{short} = 0.3\Omega \Rightarrow 1 - \eta = 10\%$

- Traditional design: dead time is insured based on margining worst case delays + jitter between driver chain for each MOSFET
- Our topology can sense the effect of dead time drift due to temperature, aging or radiation so it can continuously optimize efficiency and keep dt minimum



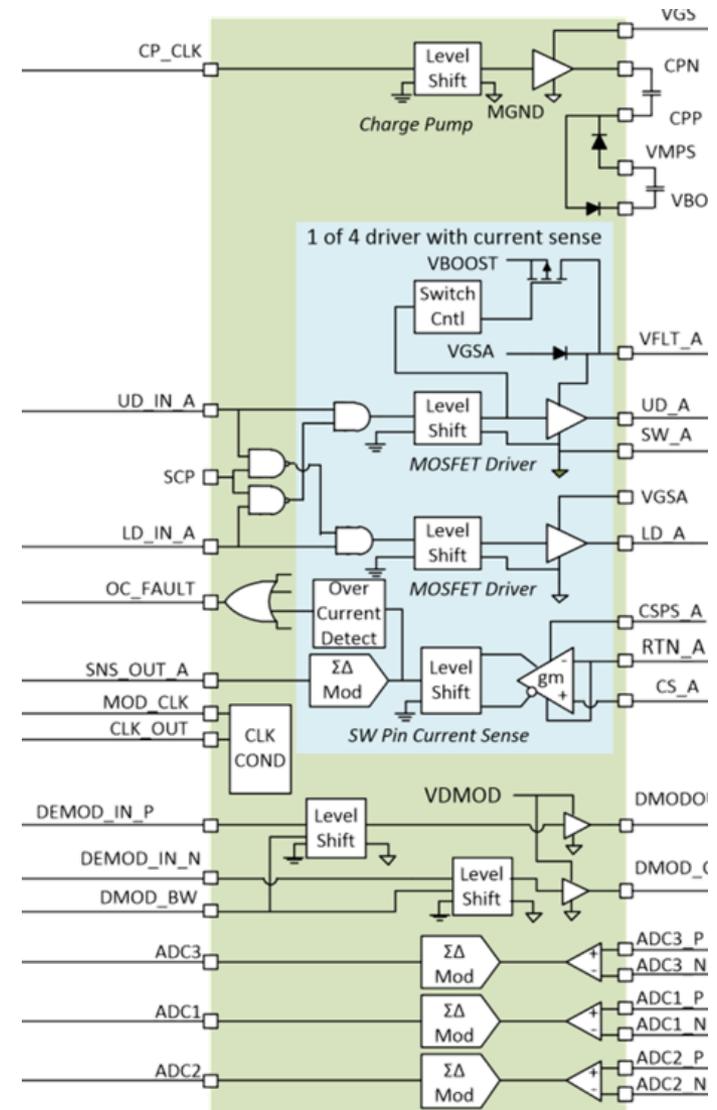
LX7720 Power Driver with Current Sensing Highlights and Applications

- Space System Manager – Motor Control – Power Management
- Motor driver Servo Control
- Linear actuator servo control
- Stepper, BLDC, PMSM motor driver
- DC/DC
- Power drivers up to 150V
- In-line Current Sense with embedded converters
- 132-lead ceramic Quad Flat Pack package - 24mmx24mm



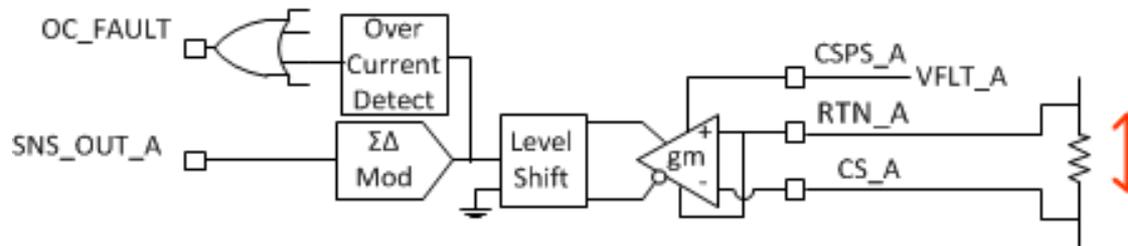
LX7720 Power Driver with Current Sensing Features

- Four Half-Bridge Nch MOSFET drivers
- Four floating differential current sensors with $\Sigma\Delta$ modulated processed outputs to FPGA
- Pulse density modulated resolver exciter
- Three differential resolver sensors with $\Sigma\Delta$ modulated processed outputs to FPGA
- Six threshold configurable logic inputs
- Ground isolation signal-to-motor
- Six bi-level logic inputs
- Fault detection
- Radiation Tolerant
 - SEL free – 87Mev-cm²/mg
 - 100krad TID
 - ELDRS tested up to 50krads



LX7720 Floating Current Sense

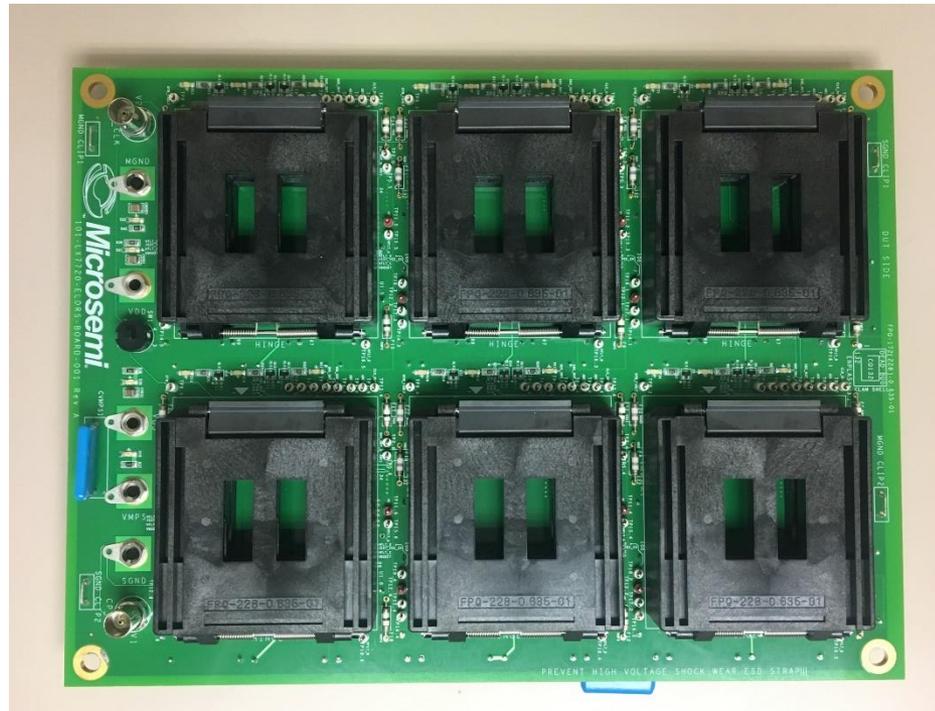
- Capable of sensing current at the switch pin; this gives a true indication of coil current.
- Senses a +/-250mV differential analog signal. Rejects a common mode signal of 150Vpk changing at a rate of 15KV/us.
- Single line sigma delta data stream output to FPGA
- 2nd order sigma delta modulator at 32MHz
- Provides OC fault detection for levels exceeding 300mV



Floating Current Sense

LX7720 Radiation testing schedule

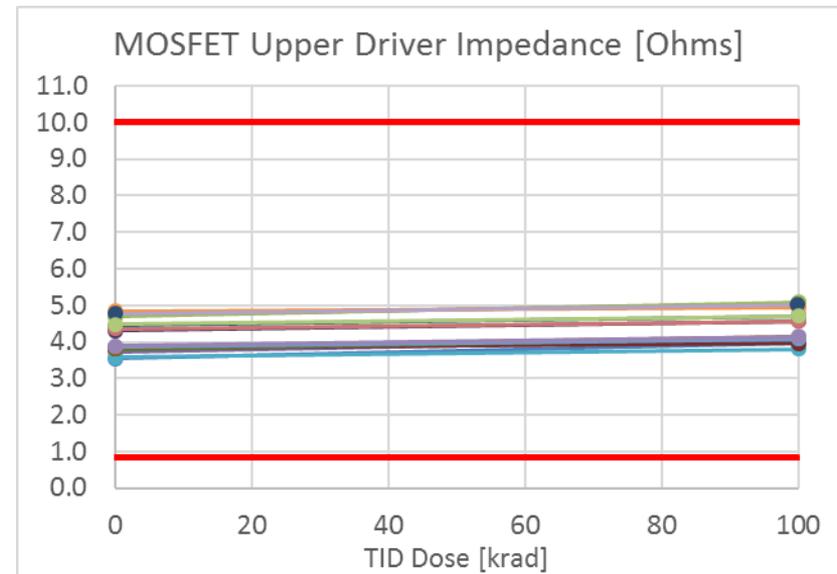
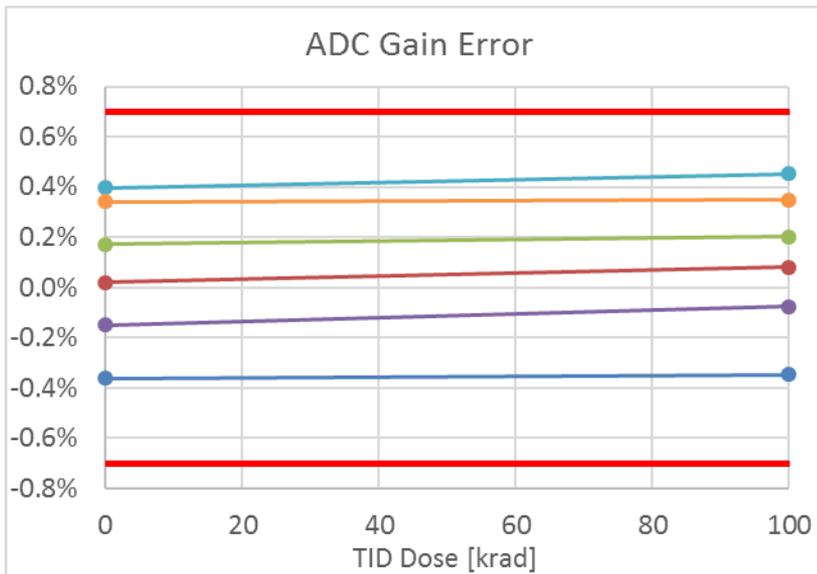
- Preliminary 100krad test performed at DMEA in May 2018
- Final 100krad test under way. Data will be presented at NSREC
- 100krad test of qual lot to be completed in November 2018
- 50krad ELDRS to be completed in February 2019
- SEE testing scheduled for end of June, data will be presented at RADECS



LX7720 TID 100krad

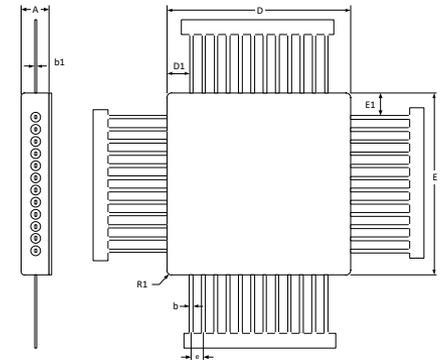
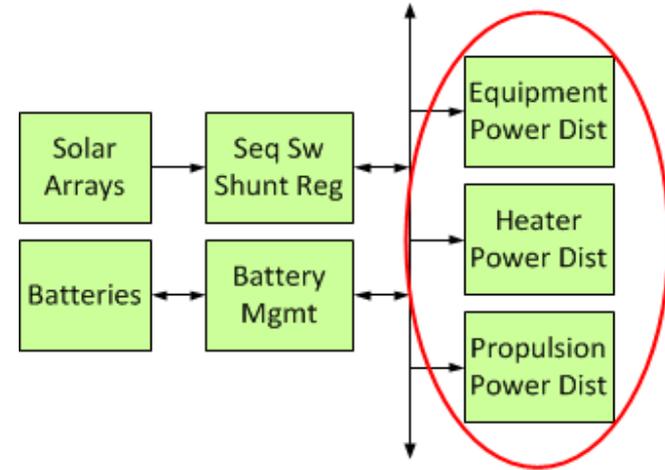
■ Preliminary 100krad results:

- No significant shifts observed on the following parameters:
 - Current consumption
 - Reference voltage
 - Fault thresholds
 - Bi-level inputs and logic I/O parameters
 - ADC gain
- Small increase, 5-10%, in the MOSFET and DMOD drivers impedance
- Small degradation of ADC offset ($<0.15\%FSR$)



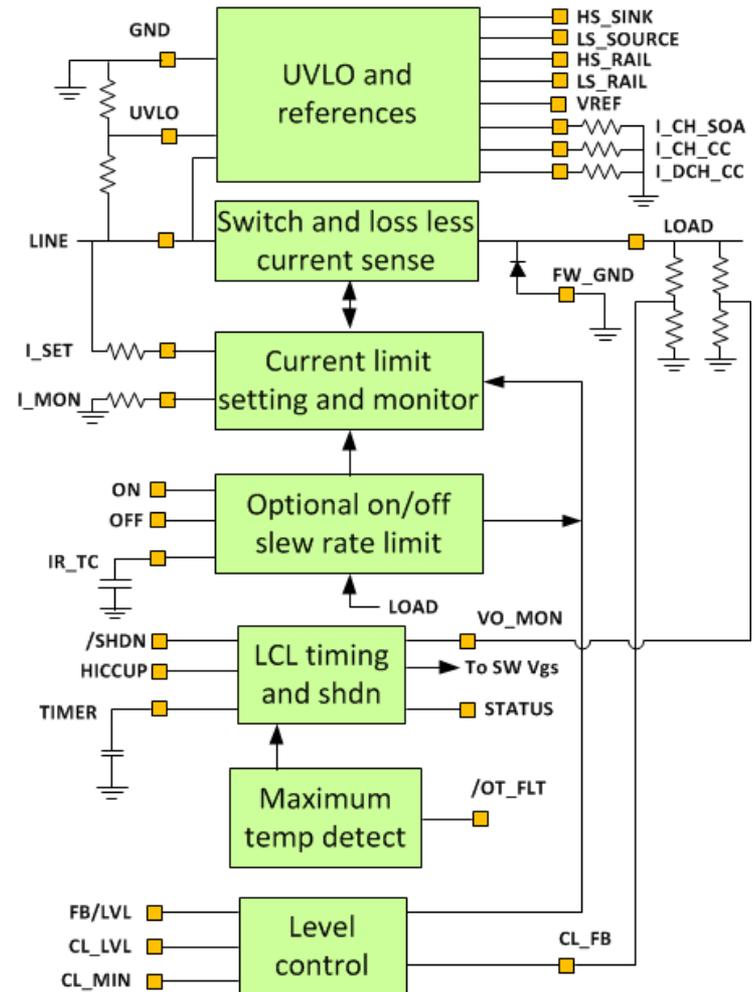
LX7712 Power Line Protector Device Highlights and Applications

- Used for power control and distribution
 - Provides a protected integrated switch
 - Turns on and off DC load with current of up to 5A
 - Latch-able current limit protection
 - Fold-back current limit protection
 - Can be paralleled for higher currents
 - 48-lead hermetic HTF flatpack package - 19mmx19mm
-
- ESA Standards:
 - ECSS-E-HB-20-20A: Electrical design and interface requirements for power supply
 - ECSS-E-ST-20-20C: Guidelines for electrical design and interface requirements for power supply

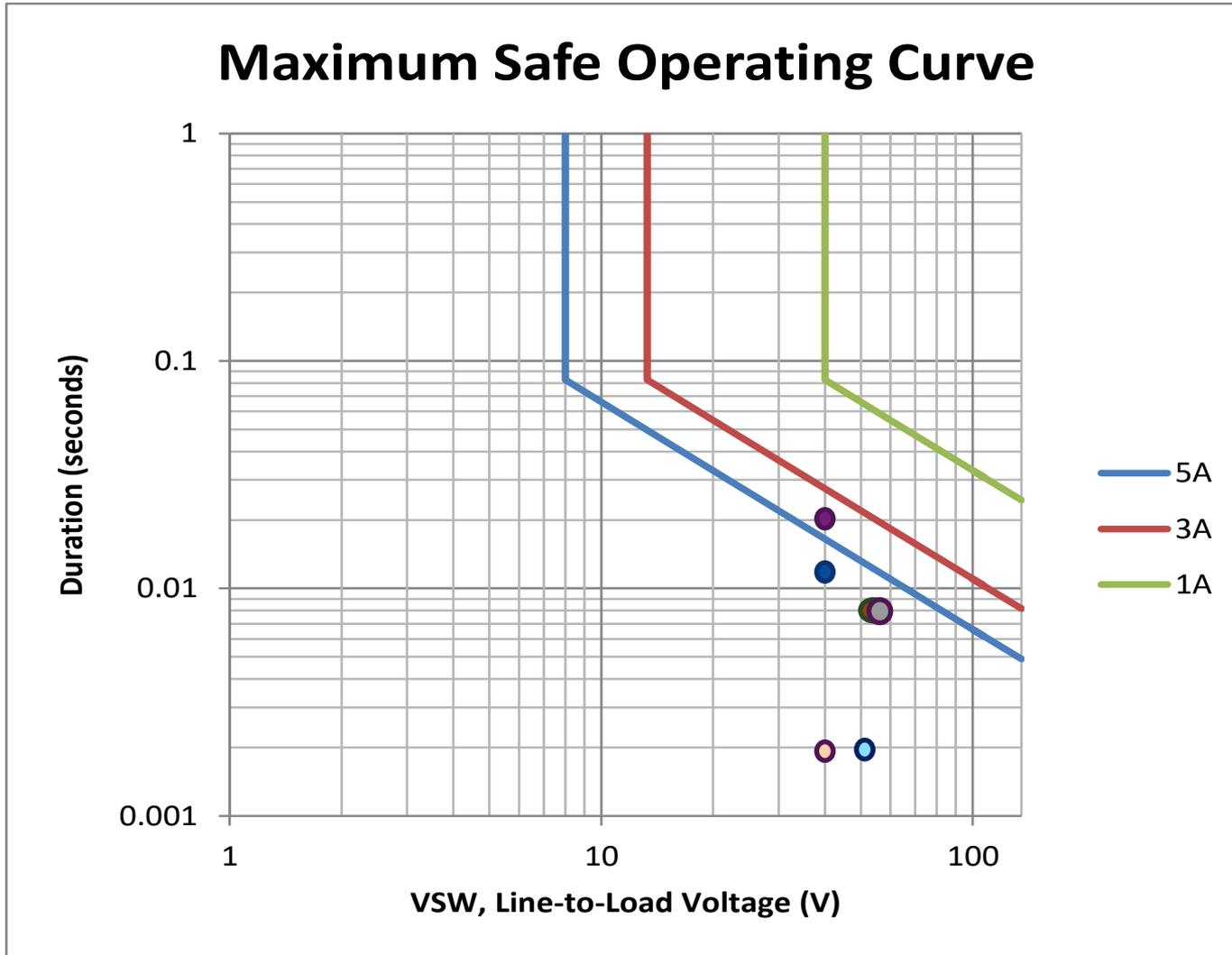


LX7712 Power Line Protector Device Features

- Internal 5A PMOS switch and catch diode
- 120V rated
- LCL or FCL configurable
- ON, OFF, and STATUS pins
- Programmable UVLO and current levels
- Current monitor output
- Current slew rate control: on and off
- Programmable timer
- Optional hiccup restart mode
- Temperature shutdown - optional
- Radiation Tolerant
 - SEL free – 87Mev-cm2/mg
 - 100krad TID
 - ELDRS tested up to 50krads



LX7712 Power Line Protector Device Classification as LCL, HLCL & RLCL



LEGEND:

- RLCL 2B (38V, 2.2-2.8A, 10-20ms)
- RLCL 2(52V, 2.2-2.8A, 4-8ms)
- LCL 4(38V, 4.4-5.6A, 6-12ms)
- LCL 4B(52V, 4.4-5.6A, 4-8ms)
- HLCL 4(38V, 4.4-5.6A, 0.5-2ms)
- HLCL 4(52V, 4.4-5.6A, 0.5-2ms)

Note: for LCL and HLCL classification the max current limit needs to be set between 4.4-5A for LX7712

DC/DC control

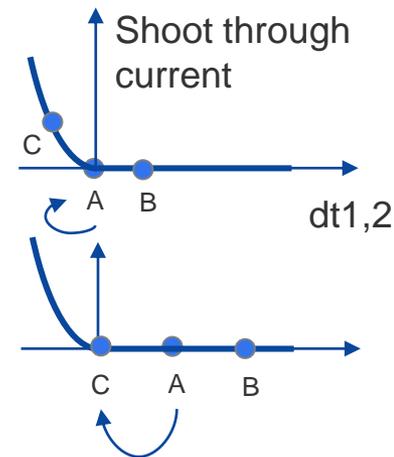
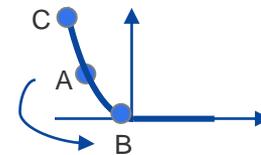
- Fast loop / slow loop approach
 - Fast loop implements a PID controller for each of the two boost DC/DC converters served by each LX7720
 - PID controller at switching frequency regulates voltage across the input PV string to a target voltage by controlling the duty cycle, bandwidth 5-10x switching frequency.
 - Power stage SOA sensing can overwrite the target
 - Slow loop is an integral controller updating the target voltage of the fast loop in order to optimize the input power (MPPT), bandwidth 100x switching frequency (1kHz)
 - Simple “perturb and observe” or more complex (see paper references)

Dead time control

- Dead time (dt) optimization (and redundant fault monitoring) is running at a much slower pace than slow loop (e.g. 1Hz)
- Optimization based on perturb and observe method using the fact that the only observable degradation is at negative dt.

1. Start from A and test B and C

- If $C \gg A \approx B$ stay in A
- If $C \gg A \gg B$ move to B
- If $C \approx A \approx B$ move to C
- If $C < A$ or $A < B$ error, set conservative dt

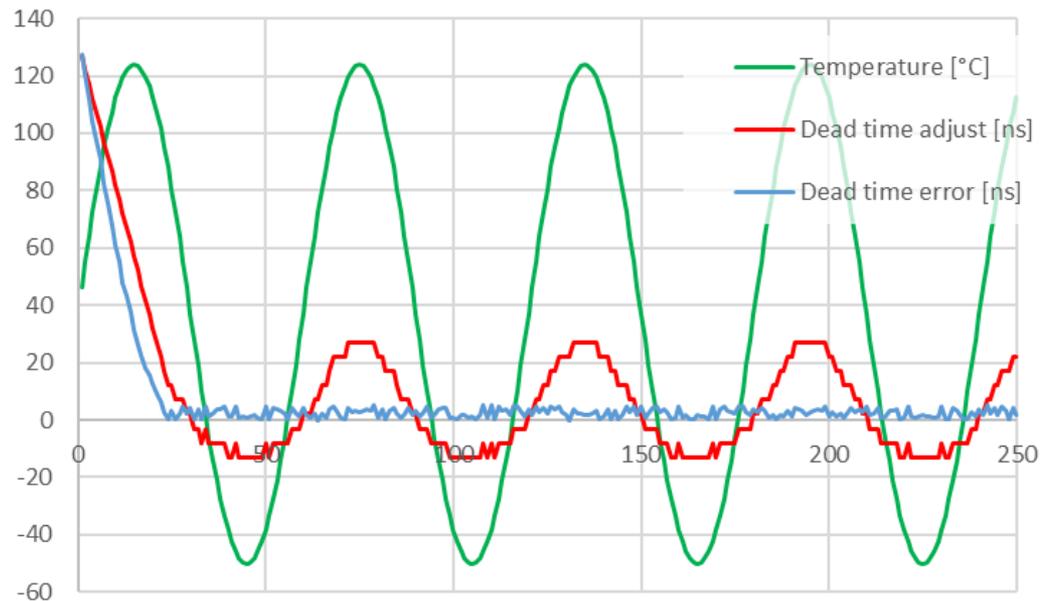


2. Repeat 1.

Dead time loop modeling

- Modeled dead time adjustment control and a delay mismatch temperature model to verify operation.
- Simulation: response to thermal cycles.

- Dead time adjustments are done at the level of the PWMs driving the higher and lower MOSFETs
- PWM delay resolution is 5ns
- Dead time adjust is the extra delay added to the nominal rising edge of the upper MOSFET gate driver.
- Dead time error is the difference between ideal dead time adjust and current dead time
- Initial safe dead time adjustment is 125ns



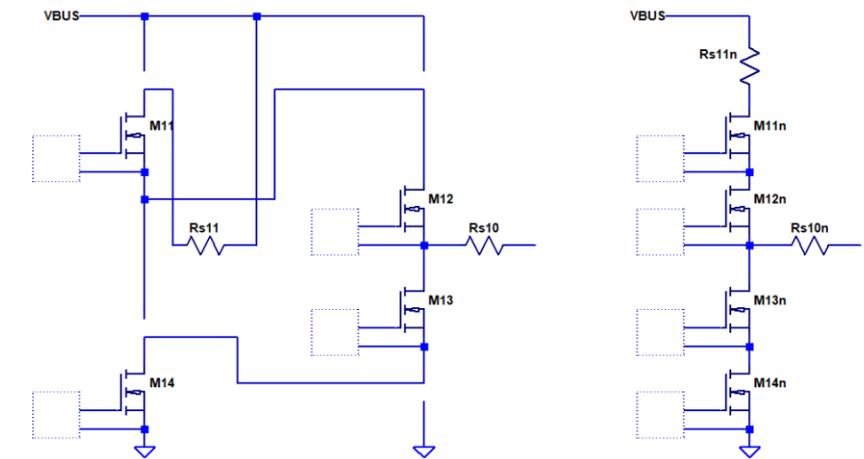
Experimental data

- LX7720 motor control evaluation



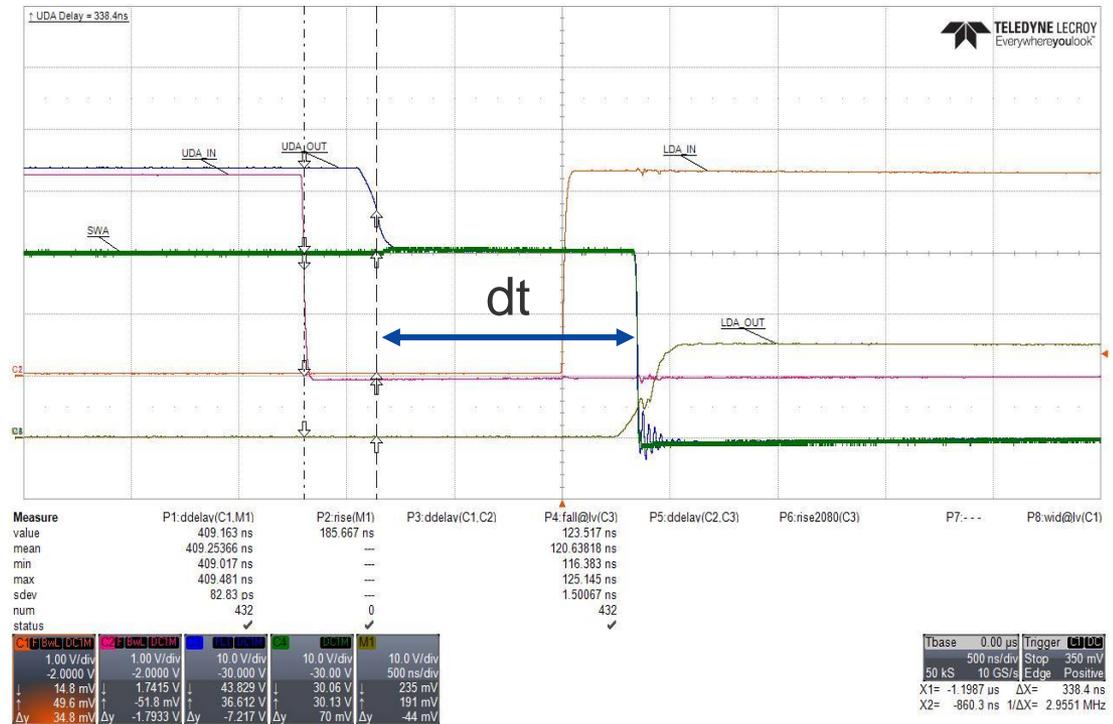
- Modification to evaluate the new power stage

Two half bridge circuits reconnected



Experimental data cont.

- In a conservative design to margin for TID and temperature variation of the 7720 and MOSFETs dt is set to 1.2 μ s.
 - If we want duty cycle up to 10% then dt margin is maximum 5% $\Rightarrow T_{sw} = 24\mu$ s
 - If we use dt control with a step of 5ns then dt becomes negligible
 - the new limiting factor will be the gate driver minimum pulse width (~ 500 ns) and $T_{sw} = 5\mu$ s.
- \Rightarrow 5x higher switching frequency possible with dt control.



Conclusions and future work

- In this presentation we have shown:
 - A new PMAD topology
 - A 4-MOSFET Fault Tolerant Power Stage
 - How to use LX7720 as analog front-end for DC/DC conversion using the fault tolerant power stage
 - How to apply LX7712 as power line protection for this particular PMAD
 - Details of the system control aspects:
 - How to detect faults and switch to redundant system
 - How to constantly optimize deadtime and be tolerant to parametric shift of MOSFET control delay

Conclusions and future work

- Future integration in an application/evaluation board once the LX7712 is available.
- System verification:
 - Emulate
 - loads and load faults using programmable loads
 - sources by using a PV simulator
 - Use an NI box to control the sources and loads and measure performance, behavior and fault tolerance



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Microsemi Headquarters

One Enterprise, Aliso Viejo, CA 92656 USA

Within the USA: +1 (800) 713-4113

Outside the USA: +1 (949) 380-6100

Sales: +1 (949) 380-6136

Fax: +1 (949) 215-4996

email: sales.support@microsemi.com

www.microsemi.com

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